

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2SC4667

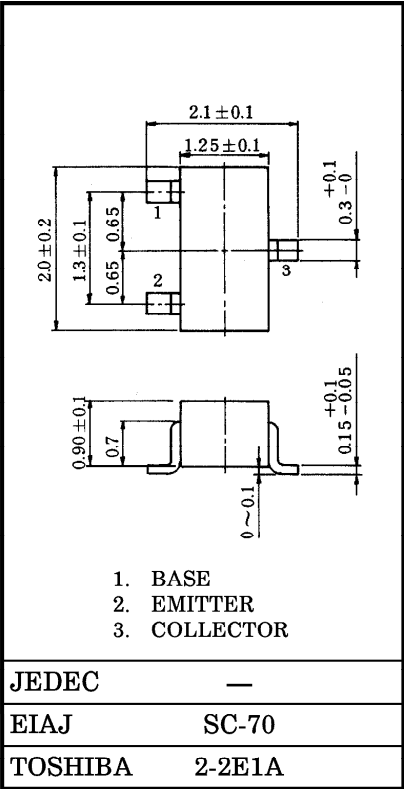
ULTRA HIGH SPEED SWITCHING APPLICATIONS.
COMPUTER, COUNTER APPLICATIONS.

Unit in mm

- High Transition Frequency : $f_T=400\text{MHz}$ (Typ.)
- Low Saturation Voltage : $V_{CE}(\text{sat})=0.3\text{V}$ (Max.)
- High Speed Switching Time : $t_{\text{stg}}=15\text{ns}$ (Typ.)

MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	200	mA
Base Current	I_B	40	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	$-55\sim 125$	$^\circ\text{C}$



Weight : 0.006g

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		ICBO	V _{CB} = 40V, I _E = 0	—	—	0.1	μA
Emitter Cut-off Current		IEBO	V _{EB} = 5V, I _C = 0	—	—	0.1	μA
DC Current Gain	h _{FE} (1) (Note 1)		V _{CE} = 1V, I _C = 10mA	40	—	240	
	h _{FE} (2)		V _{CE} = 1V, I _C = 100mA	20	—	—	
Collector-Emitter Saturation Voltage		V _{CE} (sat)	I _C = 20mA, I _B = 1mA	—	—	0.3	V
Base-Emitter Saturation Voltage		V _{BE} (sat)	I _C = 20mA, I _B = 1mA	—	—	1.0	V
Transition Frequency		f _T	V _{CE} = 10V, I _C = 10mA	200	400	—	MHz
Collector Output Capacitance		C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	4	6	pF
Switching Time	Turn-on Time	t _{on}	(Note 2)	—	70	—	ns
	Storage Time	t _{stg}		—	15	—	
	Turn-off Time	t _{off}		—	30	—	

Note 1 : h_{FE}(1) Classification R : 40~80, O : 70~140, Y : 120~240

Note 2 : SWITCHING TIME TEST CIRCUIT

